

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) 2002-249352US		Application Number <i>10/647,468</i> Not Yet Assigned	
				Applicant(s) <b>Osamu ABE</b>		Filing Date <i>8.26.03</i> Concurrently Herewith	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
<i>TLE</i>	2002-123325	04/26/2002	Japan	<i>605F</i>	<i>3/24 ABS</i>		
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
<i>TLE</i>		<i>Hitoshi Tanaka, et al., "A Precise On-Chip Voltage Generator for a Gigascale DRAM with a Negative World-Line Scheme", IEEE Journal of Solid-State Circuits, Vol. 34 No. 8, August 1999, pp 1084-1089.</i>					
EXAMINER <i>Terry L. England</i>				DATE CONSIDERED <i>8.13.04</i>			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							